Vishay Semiconductors

Ultrafast Sinterglass Rectifier

Features

- High temperature metallurgically bonded construction
- Glass passivated cavity-free junction
- Superfast recovery time for high efficiency
- Ultrafast recovery time for high efficiency
- Low forward voltage, high current capability
- Capable of meeting environmental standards of MIL-S-19500
- Hermetically sealed package
- High surge capability
- High temperature soldering guaranteed: 250 °C/

10 seconds, 0.375 $^{\rm "}$ (9.5 mm) lead length, 5 lbs. (2.3 kg) tension

Mechanical Data

Case: JEDEC DO-204AP solid glass body Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any

Weight: 560 mg

Absolute Maximum Ratings

 T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Sub type	Symbol	Value	Unit
Maximum repetitive peak reverse voltage		GI1101	V _{RRM}	50	V
		GI1102	V _{RRM}	100	V
		GI1103	V _{RRM}	150	V
		GI1104	V _{RRM}	200	V
Maximum RMS voltage		GI1101	V _{RMS}	35	V
		GI1102	V _{RMS}	70	V
		GI1103	V _{RMS}	105	V
		GI1104	V _{RMS}	140	V
Maximum DC blocking voltage		GI1101	V _{DC}	50	V
		GI1102	V _{DC}	100	V
		GI1103	V _{DC}	150	V
		GI1104	V _{DC}	200	V
Maximum average forward rectified current	0.375 " (9.5 mm) lead length (see figure 1)	GI1101	I _{F(AV)}	2.5	А
	0.375 " (9.5 mm) lead length (see figure 1)	GI1102	I _{F(AV)}	2.5	А
	0.375 " (9.5 mm) lead length (see figure 1)	GI1103	I _{F(AV)}	2.5	А
	0.375 " (9.5 mm) lead length (see figure 1)	GI1104	I _{F(AV)}	2.0	А
Peak forward surge current	8.3 ms single half sine-wave superimposed on rated load (JEDEC Method), at rated T _L		I _{FSM}	50	А



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Parts Table

Part	Type differentiation				
GI1101	V _{RRM} = 50 V				
GI1102	V _{RRM} = 100 V				
GI1103	V _{RRM} = 150 V				
GI1104	V _{RRM} = 200 V				



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Maximum Thermal Resistance

 $T_{amb} = 25 \ ^{\circ}C$, unless otherwise specified

Parameter	Test condition	Sub type	Symbol	Value	Unit
Typical thermal resistance ^{1), 2)} - junction to ambient			R _{θJA}	65	°C/W
Typical thermal resistance ^{1), 2)} - junction to lead			R _{θJL}	20	°C/W
Operating junction and storage temperature range		GI1101	T _J , T _{STG}	- 65 to + 175	°C
		GI1102	T _J , T _{STG}	- 65 to + 175	°C
		GI1103	T _J , T _{STG}	- 65 to + 175	°C
		GI1104	T _J , T _{STG}	- 65 to + 150	°C

¹⁾ Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length and mounted on P.C.B. with 0.5 x 0.5" (12 x 12 mm) copper pads

²⁾Thermal resistance from junction to lead at 0.375" (9.5mm) lead length with both leads attached to heatsinks

Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Sub type	Symbol	Min	Тур.	Max	Unit
Maximum instantaneous forward voltage	I _F = 2.0 A	GI1101	V _F			0.95	V
	I _F = 2.0 A	GI1102	V _F			0.95	V
	I _F = 2.0 A	GI1103	V _F			0.95	V
	I _F = 2.0 A	GI1104	V _F			1.25 ¹⁾	V
Maximum reverse recovery time	$I_F = 0.5 \text{ A}, I_R = 1.0 \text{ A}, I_{rr} = 0.25 \text{ A}$	GI1101	t _{rr}			25	ns
	$I_F = 0.5 \text{ A}, I_R = 1.0 \text{ A}, I_{rr} = 0.25 \text{ A}$	GI1102	t _{rr}			25	ns
	$I_F = 0.5 \text{ A}, I_R = 1.0 \text{ A}, I_{rr} = 0.25 \text{ A}$	GI1103	t _{rr}			25	ns
	$I_F = 0.5 \text{ A}, I_R = 1.0 \text{ A}, I_{rr} = 0.25 \text{ A}$	GI1104	t _{rr}			50	ns
Typical junction capacitance	V _R = 4 V, f = 1 MHz		CJ		45		pF
Maximum DC reverse current	at rated DC blocking voltage, T_{amb} = 25 °C	GI1101	I _R			2.0	μA
	at rated DC blocking voltage, T _{amb} = 25 °C	GI1102	I _R			2.0	μA
	at rated DC blocking voltage, T _{amb} = 25 °C	GI1103	I _R			2.0	μA
	at rated DC blocking voltage, T _{amb} = 25 °C	GI1104	I _R			10	μA
	at rated DC blocking voltage, T _{amb} = 100 °C	GI1101	I _R			50	μA
	at rated DC blocking voltage, T _{amb} = 100 °C	GI1102	I _R			50	μA
	at rated DC blocking voltage, T_{amb} = 100 °C	GI1103	I _R			50	μA
	at rated DC blocking voltage, T_{amb} = 100 °C	GI1104	I _R			200	μA

¹⁾ Tested at $I_F = 1.0 \text{ A}$



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Typical Characteristics ($T_{amb} = 25^{\circ}C$ unless otherwise specified)

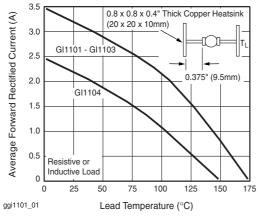


Figure 1. Maximum Forward Current Derating Curve

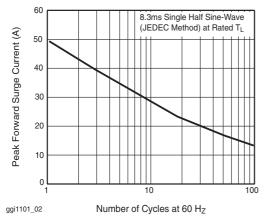


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current

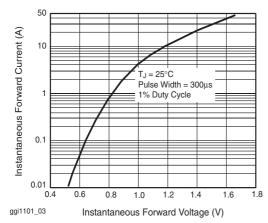


Figure 3. Typical Instantaneous Forward Characteristics

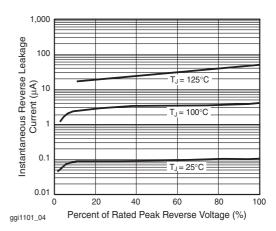


Figure 4. Typical Reverse Leakage Characteristics

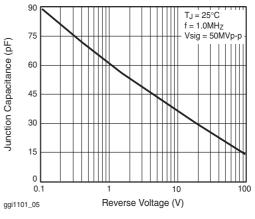
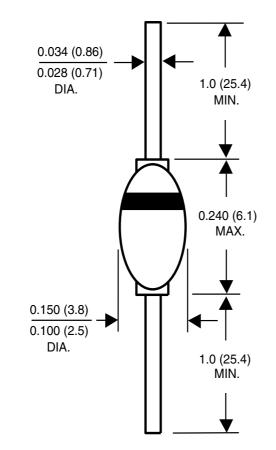


Figure 5. Typical Junction Capacitance

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Package Dimensions in mm







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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operatingsystems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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